## (19) World Intellectual Property Organization

International Bureau





(43) International Publication Date 4 August 2005 (04.08.2005)

PCT

(10) International Publication Number WO 2005/071608 A1

- (51) International Patent Classification7: G06K 19/077, 19/07, G091: 3/00, H011, 27/12, B42D 15/10
- (21) International Application Number:

PC17/P2005/001037

- (22) International Filing Date: 20 January 2005 (20.01.2005)
- (25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data: 2004-015449

23 January 2004 (23.01.2004)

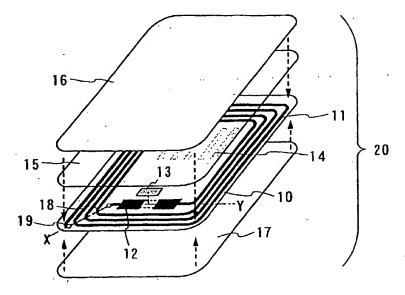
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN. CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FL GB. GD. GE, GH, GM. HR, HU, ID. IL, IN, IS, JP. KE, KG. KP, KR, KZ, LC, LK. LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GII, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,

[Continued on next page]

(54) Title: ID LABEL, ID CARD, AND ID TAG



(57) Abstract: As a non-contact ID label, ID tag and the like being widespread, it is required to manufacture a considerable quantity of ID labels at quite a low cost. An ID label attached to a product is, for example, required to be manufactured at 1 to several years each, or preferably less than one yen. Thus, such a structure and a process are demanded that an ID label can be manufactured in a large quantity at a low cost. A thin film integrated circuit device included in the ID label, the ID card, and the ID tag of the invention each includes a thin film active element such as a thin film transistor (TFT). Therefore, by peeling a substrate on which TFTs are formed for separating elements, the ID label and the like can be manufactured in a large quantity at a low cost.